

PNP EPITAXIAL PLANAR SILICON TRANSISTOR

CMMT591A SOT-23





MARKING: 59A

Complementary CMMT491A

ABSOLUTE MAXIMUM RATINGS

Collector -Base VoltageVCBOIC=100Collector -Emitter VoltageVCEOIC=100Emitter Base VoltageVEBOIE=1000Collector Cut off CurrentICBOVCB=30Emitter Cut off CurrentIEBOVEB=40Collector-Emitter Cut off CurrentICESVCE=30Collector Emitter Saturation VoltageVCE(Sat)*IC=1000Base Emitter Saturation VoltageVBE(Sat)*IC=1A,DC Current GainhFEIC=1mAIC=1000IC=1000IC=1000IC=1000IC=1000IC=1000IC=1000IC=1000	IÁ, IC=0 5.0)V, IE=0 - /, IC=0 -	50 MAX - - 100 100 100 100	V V A A MA mW deg C V V V V V NA nA
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Collector -Base VoltageVCBOIC=1000Collector -Emitter VoltageVCEOIC=1000Emitter Base VoltageVEBOIE=1000Collector Cut off CurrentICBOVCB=30Emitter Cut off CurrentIEBOVEB=40Collector-Emitter Cut off CurrentICESVCE=30Collector Emitter Saturation VoltageVCE(Sat)*IC=1000IC=5000IC=5000IC=1A,Base Emitter Saturation VoltageVBE(Sat)*IC=1A,DC Current GainhFEIC=1mAIC=1000IC=1000	JA, IE=0 40 A, IB=0 40 IA, IC=0 5.0 JV, IE=0 - /, IC=0 -	- - 100 100	V V V nA
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Emitter Base VoltageVEBOIE=1000Collector Cut off CurrentICBOVCB=30Emitter Cut off CurrentIEBOVEB=44Collector-Emitter Cut off CurrentICESVCE=30Collector Emitter Saturation VoltageVCE(Sat)*IC=1000IC=1A,IC=1A,IC=1A,Base Emitter on VoltageVBE(Sat)*IC=1A,DC Current GainhFEIC=1mAIC=1000IC=1000	IÁ, IC=0 5.0)V, IE=0 - /, IC=0 -	- 100 100	V nA
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Collector-Emitter Cut off Current Collector Emitter Saturation VoltageICES VCE(Sat)*VCE=30 IC=100 IC=5000 IC=1A,Base Emitter Saturation Voltage Base Emitter on VoltageVBE(Sat)*IC=100 IC=1A,DC Current GainhFEIC=1mA IC=100			nΔ
Collector Emitter Saturation VoltageVCE(Sat)*IC=100IC=5000IC=1A,Base Emitter Saturation VoltageVBE(Sat)*IC=1A,Base Emitter on VoltageVBE(on)*IC=1A,DC Current GainhFEIC=1mAIC=1000IC=1000		100	114
IC=5000IC=1A,Base Emitter Saturation VoltageVBE(Sat)*IC=1A,VBE(on)*IC=1A,VBE(on)*IC=1A,IC=1mAIC=1000)V, VBE=0 -	100	nA
Base Emitter Saturation VoltageVBE(Sat)*IC=1A,Base Emitter on VoltageVBE(on)*IC=1A,DC Current GainhFEIC=1mAIC=100IC=100	mA,IB=1mA -	0.20	V
Base Emitter Saturation VoltageVBE(Sat)*IC=1A,Base Emitter on VoltageVBE(on)*IC=1A,DC Current GainhFEIC=1mAIC=100IC=100	mA,IB=20mA -	0.35	V
Base Emitter on VoltageVBE(on)*IC=1A,DC Current GainhFEIC=1mAIC=100IC=100	B=100mA -	0.50	V
DC Current GainhFEIC=1mAIC=100IC=100	IB=50mA -	1.1	V
IC=100	VCE=5V -	1.0	V
	,VCE=5V 300	-	
IC-500	mA,VCE=5V* 300	800	
10-500	mA,VCE=5V* 250	-	
IC=1A,	VCE=5V* 160	-	
IC=2A,	VCE=5V* 30	-	
Dynamic Characteristics			
Transition FrequencyftVCE=10f=100M)V,IC=50mA, 150 Hz	-	MHz
Output Capacitance Cobo VCB=10 f=1MHz		10	pF

SOT-23 Formed SMD Package

SOT-23 Package Reel Information Reel specifications for W" Packing (13" reel)



- 4. Three consecutive empty places might be found provided this gap is followed by 6 consecutive devices.
- 5. The carrier tape (leader) starts with at least 75 empty positions (equivalent to 330 mm). In order to fix the carrier tape a self adhesive tape of 20 to 50 mm is applied. At the end of the bandolier at least 40 empty positions (equivalent to 160 mm) are there.

Tape Specification for SOT-23 Surface Mount Device



Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
SOT-23 T&R	3K/reel 10K/reel	136 gm/3K pcs 415 gm/10K pcs	3" x 7.5" x 7.5" 9" x 9" x 9" 13" x 13" x 0.5"	12.0K 51.0K 10.0K	17" x 15" x 13.5" 19" x 19" x 19" 17" x 15" x 13.5"	192.0K 408.0K 300.0K	12 kgs 28 kgs 16 kgs

Customer Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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Data Sheet